

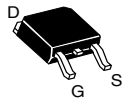
## Power MOSFET



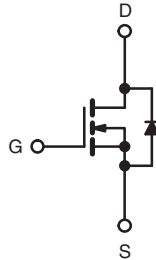
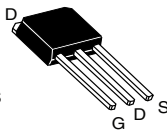
RoHS  
COMPLIANT  
HALOGEN  
**FREE**  
Available

PRODUCT SUMMARY		
$V_{DS}$ (V)	60	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 5.0$ V	0.10
$Q_g$ (Max.) (nC)	18	
$Q_{gs}$ (nC)	4.5	
$Q_{gd}$ (nC)	12	
Configuration	Single	

DPAK  
(TO-252)



IPAK  
(TO-251)



N-Channel MOSFET

### FEATURES

- Dynamic  $dV/dt$  Rating
- Surface Mount (IRLR024, SiHLR024)
- Straight Lead (IRLU024, SiHLU024)
- Available in Tape and Reel
- Logic-Level Gate Drive
- $R_{DS(on)}$  Specified at  $V_{GS} = 4$  V and 5 V
- Fast Switching
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRLU, SiHLU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface mount applications.

ORDERING INFORMATION				
Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and Halogen-free	-	SiHLR024TRL-GE3	SiHLR024TR-GE3	SiHLU024-GE3
Lead (Pb)-free	IRLR024PbF	-	IRLR024TRPbF <sup>a</sup>	IRLU024PbF
	SiHLR024-E3	-	SiHLR024T-E3 <sup>a</sup>	SiHLU024-E3

#### Note

- a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$		60	V
Gate-Source Voltage	$V_{GS}$		$\pm 10$	
Continuous Drain Current	$V_{GS}$ at 5.0 V	$T_C = 25$ °C	14	A
		$T_C = 100$ °C	9.2	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$		56	W/°C
Linear Derating Factor			0.33	
Linear Derating Factor (PCB Mount) <sup>e</sup>			0.020	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$		91	mJ
Maximum Power Dissipation	$T_C = 25$ °C		42	W
Maximum Power Dissipation (PCB Mount) <sup>e</sup>	$T_A = 25$ °C		2.5	
Peak Diode Recovery $dV/dt$ <sup>c</sup>	$dV/dt$		4.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$		- 55 to + 150	°C
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s		260	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$  V, starting  $T_J = 25$  °C,  $L = 541$   $\mu$ H,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 14$  A (see fig. 12).
- $I_{SD} \leq 17$  A,  $dI/dt \leq 140$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).



THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	$R_{thJA}$	-	-	50	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	-	3.0	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.068	-	V/ $^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.0	-	2.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 10\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 5.0\text{ V}$	$I_D = 8.4\text{ A}^b$	-	-	0.10	$\Omega$
		$V_{GS} = 4.0\text{ V}$	$I_D = 7.0\text{ A}^b$	-	-	0.14	
Forward Transconductance	$g_{fs}$	$V_{DS} = 25\text{ V}, I_D = 8.4\text{ A}^b$		7.3	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$		-	870	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	360	-	
Reverse Transfer Capacitance	$C_{riss}$			-	53	-	
Total Gate Charge	$Q_g$	$V_{GS} = 5.0\text{ V}$	$I_D = 17\text{ A}, V_{DS} = 48\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	18	nC
Gate-Source Charge	$Q_{gs}$			-	-	4.5	
Gate-Drain Charge	$Q_{gd}$			-	-	12	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, I_D = 17\text{ A}, R_g = 9.0\text{ }\Omega, R_D = 1.7\text{ }\Omega, \text{ see fig. 10}^b$		-	11	-	ns
Rise Time	$t_r$			-	110	-	
Turn-Off Delay Time	$t_{d(off)}$			-	23	-	
Fall Time	$t_f$			-	41	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact <sup>c</sup>		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode		-	-	14	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	56	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 14\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 17\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	260	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.75	1.5	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

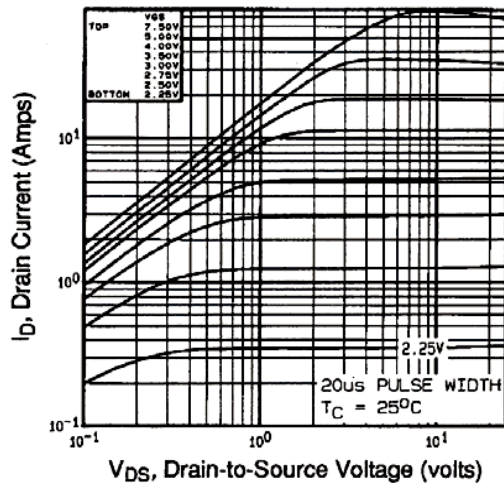


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

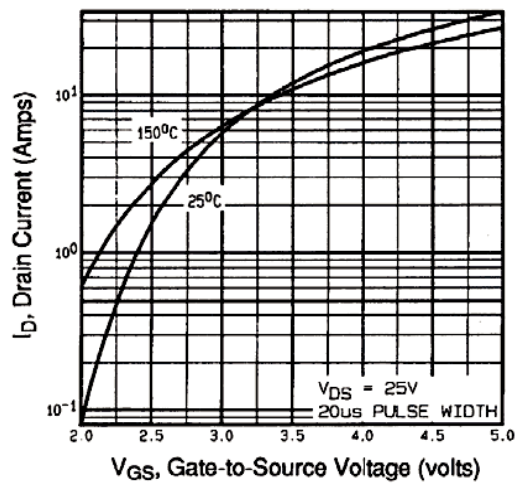


Fig. 3 - Typical Transfer Characteristics

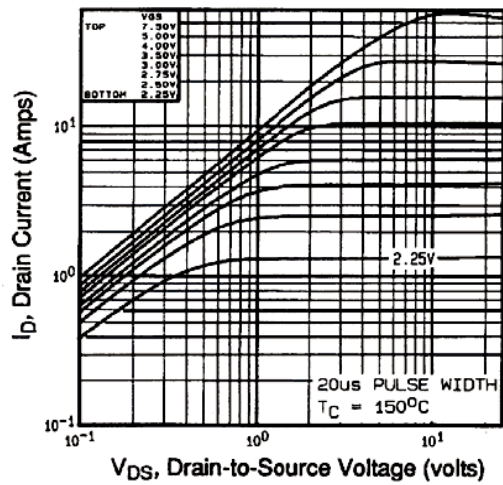


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

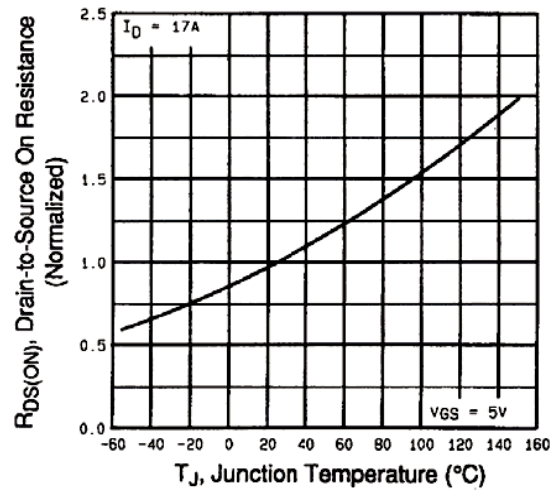


Fig. 4 - Normalized On-Resistance vs. Temperature

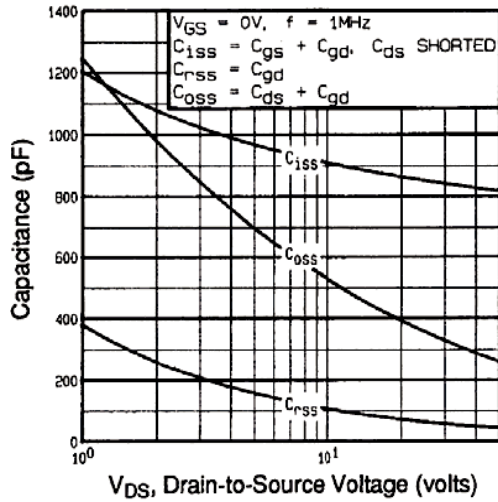


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

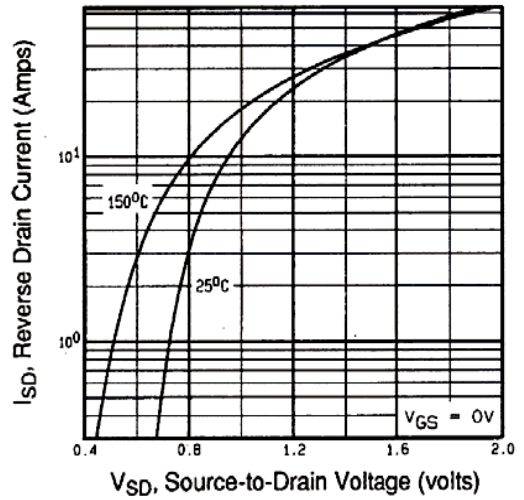


Fig. 7 - Typical Source-Drain Diode Forward Voltage

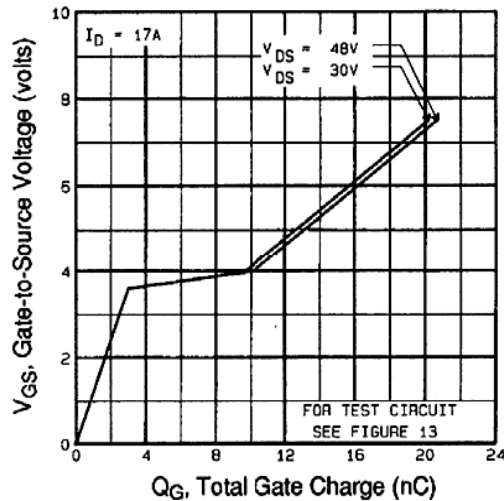


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

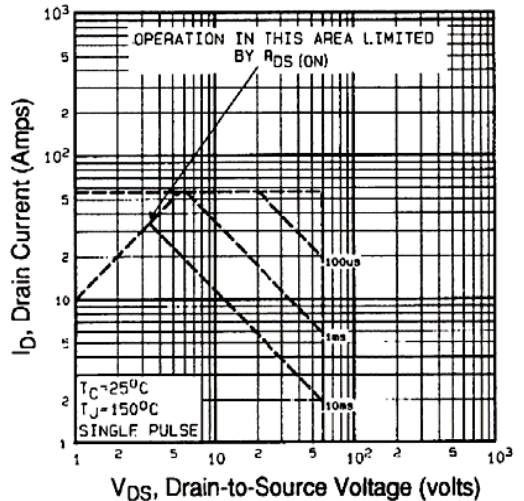


Fig. 8 - Maximum Safe Operating Area

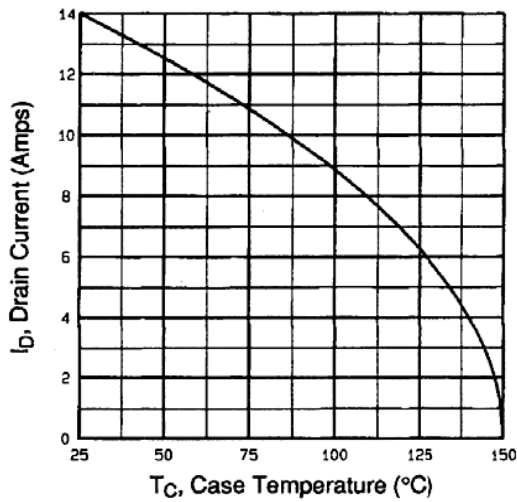


Fig. 9 - Maximum Drain Current vs. Case Temperature

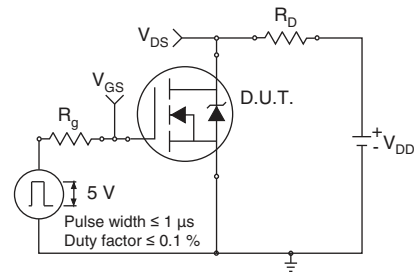


Fig. 10a - Switching Time Test Circuit

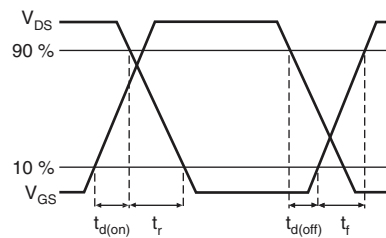


Fig. 10b - Switching Time Waveforms

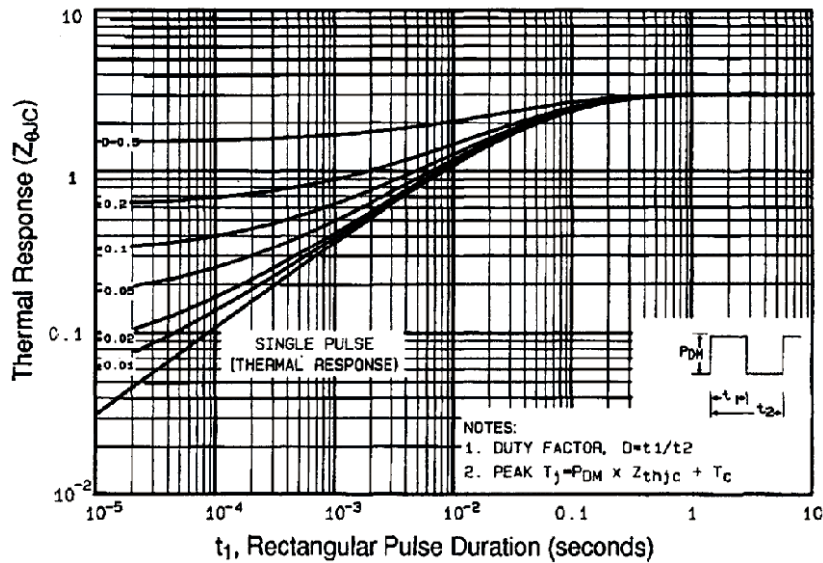


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

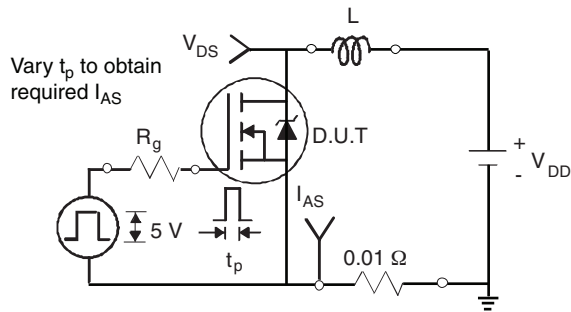


Fig. 12a - Unclamped Inductive Test Circuit

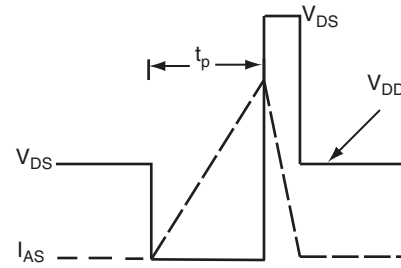


Fig. 12b - Unclamped Inductive Waveforms

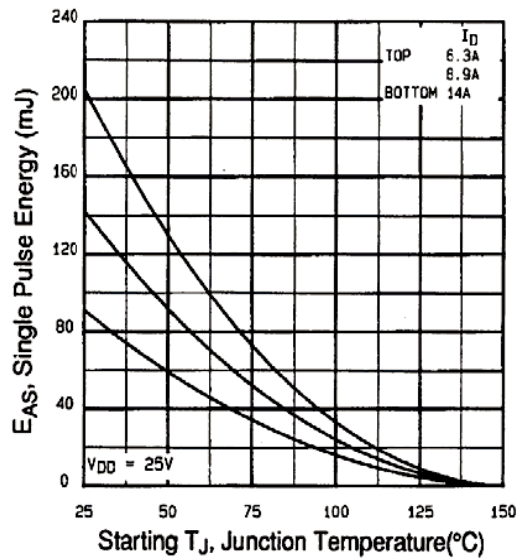


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

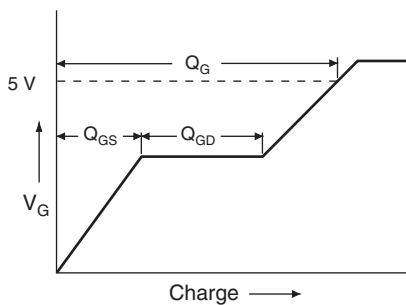


Fig. 13a - Basic Gate Charge Waveform

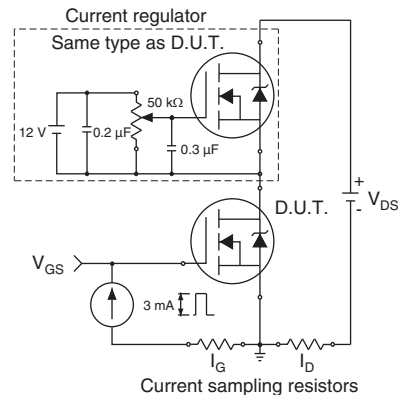
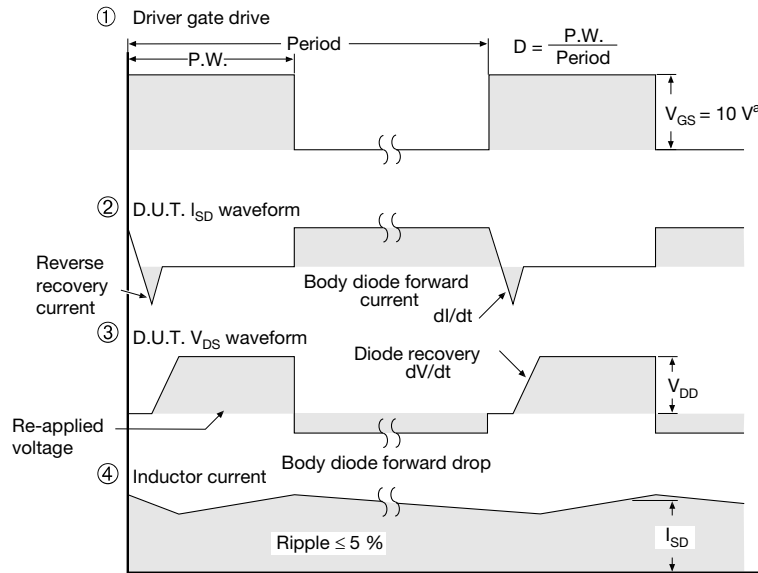
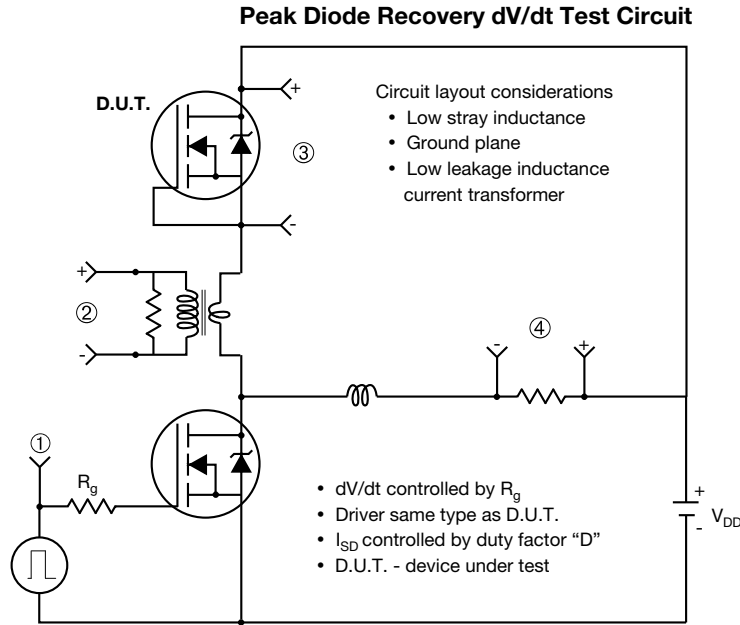


Fig. 13b - Gate Charge Test Circuit

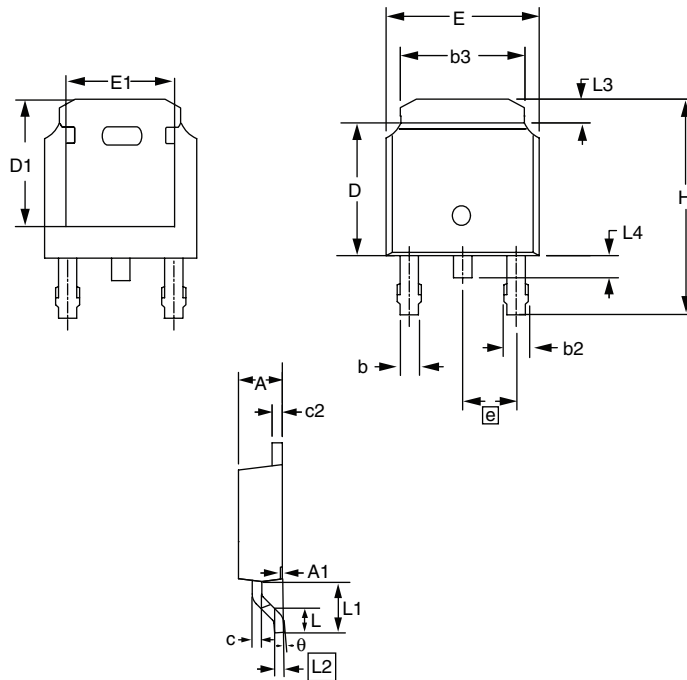


**Note**  
 a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91322](http://www.vishay.com/ppg?91322).

## TO-252AA (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
E	6.40	6.73	0.252	0.265
L	1.40	1.77	0.055	0.070
L1	2.743 REF		0.108 REF	
L2	0.508 BSC		0.020 BSC	
L3	0.89	1.27	0.035	0.050
L4	0.64	1.01	0.025	0.040
D	6.00	6.22	0.236	0.245
H	9.40	10.40	0.370	0.409
b	0.64	0.88	0.025	0.035
b2	0.77	1.14	0.030	0.045
b3	5.21	5.46	0.205	0.215
e	2.286 BSC		0.090 BSC	
A	2.20	2.38	0.087	0.094
A1	0.00	0.13	0.000	0.005
c	0.45	0.60	0.018	0.024
c2	0.45	0.58	0.018	0.023
D1	5.30	-	0.209	-
E1	4.40	-	0.173	-
θ	0'	10'	0'	10'

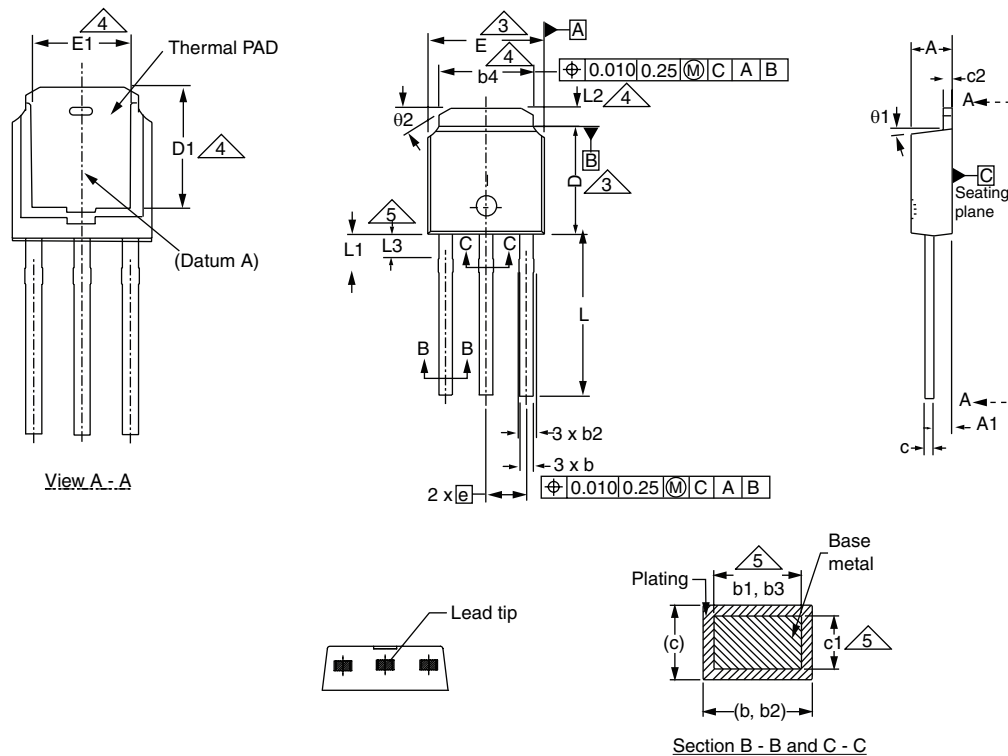
ECN: S-81965-Rev. A, 15-Sep-08  
DWG: 5973

### Notes

1. Package body sizes exclude mold flash, protrusion or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 0.10 mm per side.
2. Package body sizes determined at the outermost extremes of the plastic body exclusive of mold flash, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. The package top may be smaller than the package bottom.
4. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.10 mm total in excess of "b" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot.



### TO-251AA (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

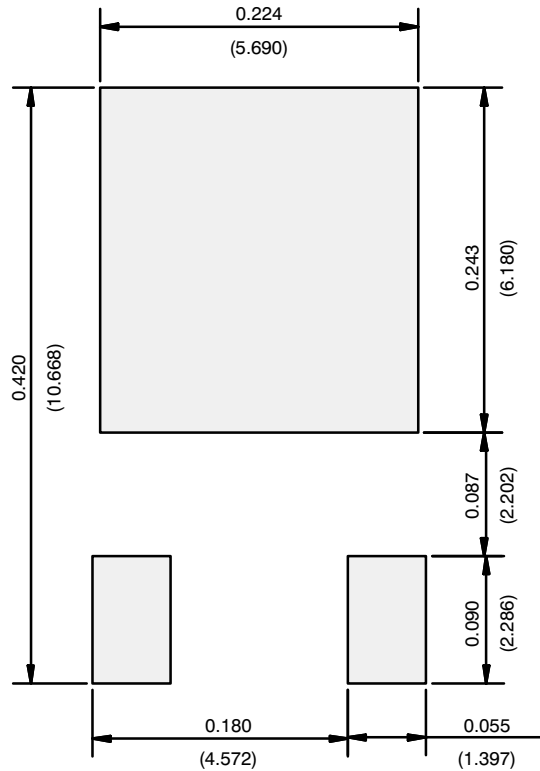
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
theta1	0'	15'	0'	15'
theta2	25'	35'	25'	35'

ECN: S-82111-Rev. A, 15-Sep-08  
 DWG: 5968

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension are shown in inches and millimeters.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions b4, L2, E1 and D1.
5. Lead dimension uncontrolled in L3.
6. Dimension b1, b3 and c1 apply to base metal only.
7. Outline conforms to JEDEC outline TO-251AA.

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

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